



Product Change Notification



Product Group: DD/Wed Mar 23, 2022/PCN-DD-006-2022-REV-0

IGBT wafer diameter change in Power Modules

DESCRIPTION OF CHANGE: Change of wafer diameter of IGBT chips used in below power module.

FROM: 6 inches wafer diameter TO: 8 inches wafer diameter

REASON FOR CHANGE: Obsolescence of 6 inches wafer from IGBT supplier.

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE: There will be no effect on product quality and reliability. Some variations are expected in datasheet (See Annex 1)

PART NUMBERS/SERIES/FAMILIES AFFECTED: VS-ETF075Y60U

VISHAY BRAND(s): Vishay Semiconductors

TIME SCHEDULE:

Start Shipment Date: Wed Jun 1, 2022

SAMPLE AVAILABILITY: Upon request

PRODUCT IDENTIFICATION: Batch code (contact factory for the details)

QUALIFICATION DATA: Available upon request

This PCN is considered approved, without further notification, unless we receive specific customer concerns before Mon May 30, 2022 or as specified by contract.

ISSUED BY: Fabio Bertuccio, Fabio.Bertuccio@vishay.com

For further information, please contact your regional Vishay office.

CONTACT INFORMATION:

Americas

Vishay Semiconductors
150 Motor Parkway, Suite 119
Hauppauge New York United States 11788
Diodes-Americas@vishay.com
Phone: 631 300 3816
Fax: 631 300 3843

Europe

Vishay Semiconductors
Theresienstrasse 2
Heilbronn Germany 74072
Diodes-Europe@vishay.com
Phone: +49 7131 7498 656 (715)
Fax: +49 7131 67 2938

Asia

Vishay Semiconductors
15D, Sun Tong Infoport Plaza
55 Huai Hai West Road
Shanghai China 200030
Diodes-Asia@vishay.com
Phone: +86 138 1787 2112
Fax: +86 21 5258 7979

Vishay Intertechnology, Inc.

Corporate Headquarters 63 Lincoln Highway, Malvern, PA 19355-2143 U.S.A. Phone (610) 644-1300 Fax (610) 296-0657 www.vishay.com

ONE OF THE WORLD'S LARGEST MANUFACTURERS OF DISCRETE SEMICONDUCTORS AND PASSIVE COMPONENT

ANNEX 1

VS-ETF075Y60U

| Parameter | Conditions | From: | To: |
|--|--|-------|-------|
| Continuous collector current – I_c^* | $T_c = 25^\circ\text{C}$ | 109A | 100A |
| | $T_c = 80^\circ\text{C}$ | 80A | 75A |
| Collector to emitter voltage (Max.) – Max $V_{ce(on)}$ | $V_{GE} = 15\text{ V}, I_c = 60\text{A}, T_j = 25^\circ\text{C}$ | 1.8V | 1.95V |
| | $V_{GE} = 15\text{ V}, I_c = 75\text{A}, T_j = 25^\circ\text{C}$ | 1.93V | 2.15V |

*Graphs related to these parameters will be amended accordingly

Vishay Intertechnology, Inc.

Corporate Headquarters 63 Lincoln Highway, Malvern, PA 19355-2143 U.S.A. Phone (610) 644-1300 Fax (610) 296-0657 www.vishay.com

ONE OF THE WORLD'S LARGEST MANUFACTURERS OF DISCRETE SEMICONDUCTORS AND PASSIVE COMPONENT